



Product Summary

V _(BR) dss	R _{DS(ON)} max	I _D max T _A = +25°C
60V	$7.5\Omega @ V_{GS} = 5V$	210mA

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- **Power Management Functions**

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Notes 3 & 4)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

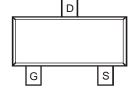


Top View

Equivalent Circuit

Gate C

Drain



Top View

Ordering Information (Note 5)

Part Number	Compliance	Case	Packaging
2N7002-7-F	Standard	SOT23	3,000/Tape & Reel
2N7002-13-F	Standard	SOT23	10,000/Tape & Reel
2N7002Q-7-F	Automotive	SOT23	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

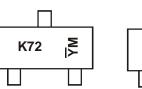
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

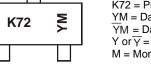
Source

4. Product manufactured with Date Code V12 (week 50, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V12 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





K72 = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Chengdu A/T Site

S

Shanghai	A/T	Site	

Date Code K	ley															
Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	Ν	Р	R	S	Т	U	V	W	Х	Y	Z	Α	В	С	D	E
Month	Jan	F	eb	Mar	Apr	M	lay	Jun	Jul	A	ug	Sep	Oct	N	ov	Dec
Code	1		2	3	4		5	6	7	8	8	9	0	1	۱ ۱	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage			V _{DSS}	60	V
Drain-Gate Voltage $R_{GS} \le 1.0M\Omega$			V _{DGR}	60	V
Gate-Source Voltage		Continuous Pulsed	V _{GSS}	±20 ±40	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$ $T_A = +100^{\circ}C$	ID	170 120 105	mA
Continuous Drain Current (Note 7) $V_{GS} = 10V$ State Steady State T _A = +25°C T _A = +85°C T _A = +100°C			ID	210 150 135	mA
Maximum Body Diode Forward Current (Note 7)	Pulsed Continuous		I _S	0.5 2	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

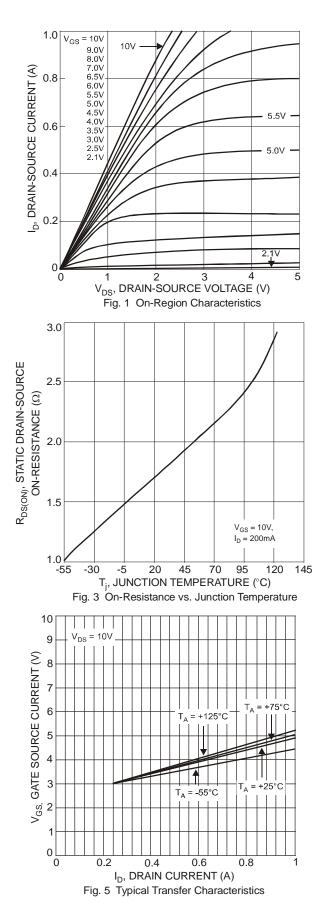
Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 6)	P	370	mW	
	(Note 7)	PD	540		
Thermal Desistance, lunction to Archiest	(Note 6)	6	348		
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	241	°C/W	
Thermal Resistance, Junction to Case	(Note 7)	R _{θJC}	91		
Operating and Storage Temperature Range	·	T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)				71	1		
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = +25°C @ T _C = +125°C	I _{DSS}	_	_	1.0 500	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage		Igss			±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)							-
Gate Threshold Voltage		V _{GS(th)}	1.0	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T _J = +25°C @ T _J = +25°C @ T _J = +125°C	R _{DS(ON)}	_	3.2 — 4.4	7.5 5.0 13.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0		Α	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance		g fs	80			mS	V _{DS} =10V, I _D = 0.2A
Diode Forward Voltage		V _{SD}	_	0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance		Ciss		22	50	pF	
Output Capacitance		Coss		11	25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance		Crss	_	2.0	5.0	pF	
Gate resistance		Rg		120		Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)		Qg	_	223	_		
Gate-Source Charge		Q _{qs}	_	82		рС	$V_{DS} = 10V, I_D = 250mA$
Gate-Drain Charge		Q _{gd}		178			
SWITCHING CHARACTERISTICS (Note 9)			-				
Turn-On Delay Time		t _{D(on)}		2.8	—		1/2 = -201/1 = -0.24
Turn-On Rise Time		tr		3.0		-	$V_{DD} = 30V, I_D = 0.2A,$ $R_I = 150\Omega, V_{GEN} = 10V,$
Turn-Off Delay Time		t _{D(off)}		7.6		$\begin{array}{c c} - & ns & R_L = 150\Omega, V_{GEN} = 1 \\ - & R_{GEN} = 25\Omega \end{array}$	
Turn-Off Fall Time		t _f	_	5.6			11GEN = 2012

6. Device mounted on FR-4 PCB, with minimum recommended pad layout
7. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing. Notes:





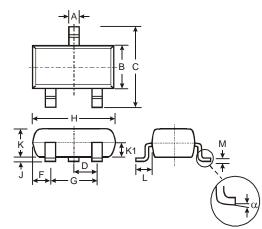
7 T_j = 25°C R_{DS(ON)}, NORMALIZED DRAIN-SOURCE 6 ON-RESISTANCE (Ω) V_{GS} = 5.0V V_{GS} = 10V 1 0 0 0.2 0.4 0.6 0.8 1.0 I_D, DRAIN CURRENT (A) Fig. 2 On-Resistance vs. Drain Current 6 R_{DS(ON)}, NORMALIZED DRAIN-SOURCE 5 **ON-RESISTANCE** (Ω) I_D = 500mA = 50mA 3 0 2 4 6 8 10 12 V_{GS}, GATE TO SOURCE VOLTAGE (V) 0 16 18 Fig. 4 On-Resistance vs. Gate-Source Voltage 400 350 P_d, POWER DISSIPATION (mW) 300 250 200 150 100 50 0 150 175 25 50 75 100 125 200 0 T_A, AMBIENT TEMPERATURE (°C)

Fig. 6 Max Power Dissipation vs. Ambient Temperature



Package Outline Dimensions

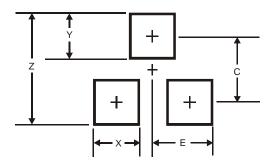
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
в	1.20	1.40	1.30					
C	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
κ	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
М	0.085	0.18	0.11					
α	0°	8°	-					
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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